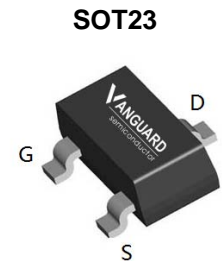


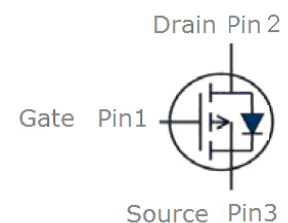
Features

- P-Channel, -5V Logic Level Control
- Enhancement mode
- Low on-resistance $R_{DS(on)}$ @ $V_{GS}=-4.5$ V
- Fast Switching
- Pb-free lead plating; RoHS compliant

V_{DS}	-100	V
$R_{DS(on),TYP}$ @ $V_{GS}=-10$ V	485	m Ω
$R_{DS(on),TYP}$ @ $V_{GS}=-4.5$ V	520	m Ω
I_D	-1.3	A



Part ID	Package Type	Marking	Tape and reel information
VSC600P10MS	SOT23	1P2	3000pcs/reel



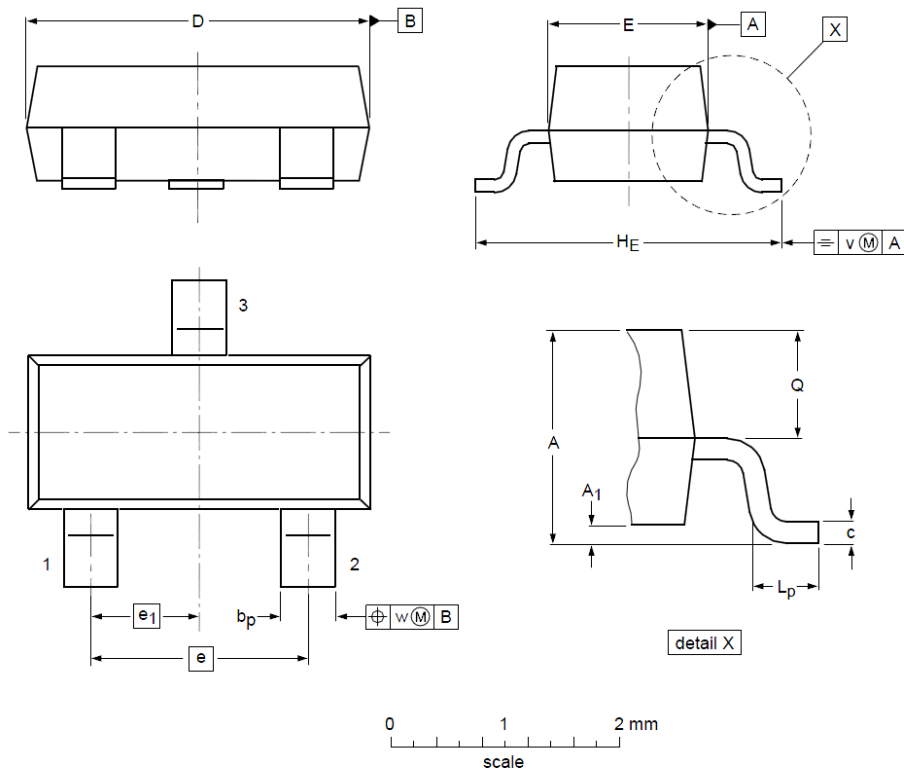
Maximum ratings, at $T_j=25$ °C, unless otherwise specified

Symbol	Parameter	Rating	Unit	
$V_{(BR)DSS}$	Drain-Source breakdown voltage	-100	V	
I_D	Continuous drain current @ $V_{GS}=-10$ V	$T_A=25$ °C	-1.3	A
		$T_A=100$ °C	-0.8	A
I_{DM}	Pulse drain current tested ①	$T_A=25$ °C	-5.2	A
P_D	Maximum power dissipation	$T_A=25$ °C	1.5	W
I_S	Diode continuous forward current	$T_A=25$ °C	1.2	A
V_{GS}	Gate-Source voltage	± 20	V	
T_{STG} T_J	Storage and operating temperature range	-55 to 150	°C	
Thermal characteristics				
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	80	°C/W	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	52	°C/W	

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_A = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(Tc=25°C)	V _{DS} =-100V,V _{GS} =0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(Tc=125°C)	V _{DS} =-100V,V _{GS} =0	--	--	-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V,V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =-250μA	-1.0	-2.0	-3.0	V
R _{DS(ON)}	Drain-Source On-State Resistance ^②	V _{GS} =-10V, I _D =-1.3A	--	485	600	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance ^②	V _{GS} =-4.5V, I _D =-1A	--	520	650	mΩ
Dynamic Electrical Characteristics @ T_A = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =-30V,V _{GS} =0V, f=1MHz	--	490	--	pF
C _{oss}	Output Capacitance		--	25	--	pF
C _{rss}	Reverse Transfer Capacitance		--	15	--	pF
Q _g	Total Gate Charge	V _{DS} =-50V,I _D =-1A, V _{GS} =-10V	--	20	--	nC
Q _{gs}	Gate-Source Charge		--	10	--	nC
Q _{gd}	Gate-Drain Charge		--	5	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =-50V, I _D =-1A, R _G =6.8Ω, V _{GS} =-10V	--	10	--	nS
t _r	Turn-on Rise Time		--	22	--	nS
t _{d(off)}	Turn-Off Delay Time		--	15	--	nS
t _f	Turn-Off Fall Time		--	11	--	nS
Source- Drain Diode Characteristics @ T_A = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =-1A,V _{GS} =0V	--	0.81	-1.2	V
t _{rr}	Reverse Recovery Time	T _J =25°C,I _{sd} =-1A, V _{GS} =0V	--	13	--	nS
Q _{rr}	Reverse Recovery Charge	di/dt=-100A/μs		22		nC

NOTE:

- ① Repetitive rating; pulse width limited by max. junction temperature.
 ② Pulse width ≤ 300μs; duty cycles ≤ 2%.

SOT23 Package Outline Data

DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.03	1.10	A₁	0.01	0.05	0.10
b_p	0.38	0.42	0.48	c	0.09	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e₁	--	0.95	--
H_E	2.10	2.40	2.50	L_p	0.15	0.23	0.45
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				

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单击下面可查看定价，库存，交付和生命周期等信息

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